Semiconductors
High-reliability discrete products and engineering services since 1977

## 1N914,A,B-1N916,A,B

## SWITCHING RECTIFIERS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.


## MAXIMUM RATINGS

| Parameter | Symbol | Value | Units |
| :--- | :---: | :---: | :---: |
| Maximum repetitive reverse voltage | $\mathrm{V}_{\text {RRM }}$ | 100 | V |
| Average rectified forward current | $\mathrm{I}_{\text {FAV })}$ | 200 | mA |
| Non-repetitive peak forward surge current <br> Pulse width $=1.0$ second <br> Pulse width $=1.0$ microsecond | $\mathrm{I}_{\text {FSM }}$ |  |  |
| Storage temperature range |  | 1.0 | A |
| Operating junction temperature | $\mathrm{T}_{\text {stg }}$ | 4.0 |  |
| Power dissipation | $\mathrm{T}_{J}$ | -65 to +200 |  |
| Thermal resistance, junction to ambient | $\mathrm{P}_{\mathrm{D}}$ | -65 to +175 | ${ }^{\circ} \mathrm{C}$ |

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Parameter |  | Symbol | Test Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Breakdown voltage |  | $V_{\text {R }}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{R}}=100 \mu \mathrm{~A} \\ & \mathrm{I}_{\mathrm{R}}=5.0 \mu \mathrm{~A} \end{aligned}$ | $\begin{gathered} 100 \\ 75 \end{gathered}$ |  | V |
| Forward voltage | 1 N 914 1 N 916 B 1N914, 1N916 1N914A, 1N916A 1 N 916 B 1 N 914 B | $V_{F}$ | $\begin{aligned} & I_{F}=5.0 \mathrm{~mA} \\ & I_{F}=5.0 \mathrm{~mA} \\ & I_{F}=10 \mathrm{~mA} \\ & I_{F}=20 \mathrm{~mA} \\ & I_{F}=20 \mathrm{~mA} \\ & I_{F}=100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 620 \\ & 630 \end{aligned}$ | $\begin{aligned} & 720 \\ & 730 \\ & 1.0 \\ & 1.0 \\ & 1.0 \\ & 1.0 \end{aligned}$ | $\begin{gathered} \mathrm{mV} \\ \mathrm{mV} \\ \mathrm{~V} \\ \mathrm{~V} \\ \mathrm{~V} \\ \mathrm{~V} \end{gathered}$ |
| Reverse current |  | $I_{\text {R }}$ | $\begin{aligned} & V_{R}=20 \mathrm{~V} \\ & V_{R}=20 \mathrm{~V}, T_{A}=150^{\circ} \mathrm{C} \\ & V_{R}=75 \mathrm{~V} \end{aligned}$ |  | $\begin{aligned} & 25 \\ & 50 \\ & 5.0 \end{aligned}$ | nA <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ |
| Total capacitance | $\begin{gathered} \text { 1N916A,B } \\ \text { 1N914A, B } \end{gathered}$ | $\mathrm{C}_{\text {T }}$ | $\begin{aligned} & V_{R}=0, f=1.0 \mathrm{MHz} \\ & V_{R}=0, f=1.0 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 2.0 \\ & 4.0 \end{aligned}$ | pF |
| Reverse recovery time |  | $\mathrm{t}_{\mathrm{rr}}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6.0 \mathrm{~V}(60 \mathrm{~mA}) \\ & \mathrm{I}_{\mathrm{rr}}=1.0 \mathrm{~mA}, \mathrm{R}_{\mathrm{L}}=100 \Omega \end{aligned}$ |  | 4.0 | ns |

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MECHANICAL CHARACTERISTICS

| Case: | DO-35 |
| :--- | :--- |
| Marking: | Body painted, alpha-numeric |
| Polarity: | Cathode band |




Figure 1. Reverse Voltage vs Reverse Current BV - 1.0 to 100 uA


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree $C$ increase in Temperature
Figure 2. Reverse Current vs Reverse Voltage IR-10 to 100 V

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Figure 4. Forward Voltage vs Forward Current VF - 0.1 to 10 mA


Figure 6. Forward Voltage vs Ambient Temperature VF - 0.01 - 20 mA ( -40 to +65 Deg C)


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Figure 8. Reverse Recovery Time vs Reverse Recovery Current


Figure 10. Power Derating Curve

Figure 9. Average Rectified Current ( $\mathrm{I}_{\text {FAVY }}$ ) versus Ambient Temperature $\left(T_{A}\right)$

